

Rapid Laser Annealing of Transparent Conductive Oxides for Temperature-Sensitive Solar Cell Structures

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In this work we address the challenge of reducing the sheet resistance R_{sheet} of transparent conductive oxide (TCO) thin films on temperature (T)-sensitive solar cell substrates. We demonstrate ultraviolet (UV) pulsed nanosecond (ns) laser annealing processes, leading to a significantly reduced R_{sheet} for different TCOs on silicon heterojunction (SHJ) substrates without compromising the implied open circuit voltage iV_{OC} . These processes offer a fast and cost efficient alternative to classical annealing processes, potentially enabling indium free TCO types on more sensitive solar cell types such as perovskite solar cells.

Motivation

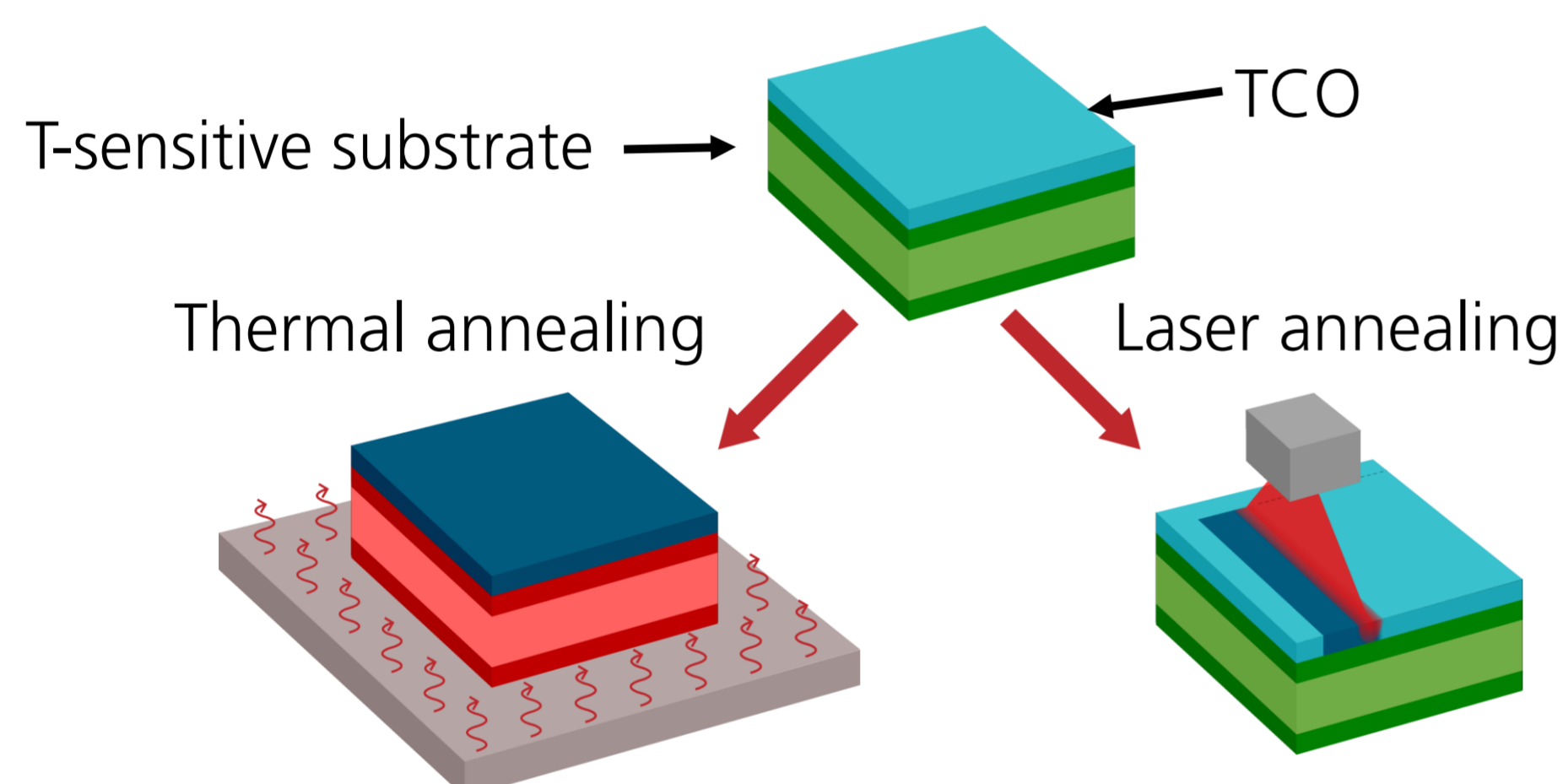


Fig. 1: Thermal annealing versus laser annealing for TCO thin films on a temperature-sensitive substrate.

Challenge:

- Annealing the TCO thin film on T-sensitive solar cells [1]
- Optimizing TCO properties [2]
- Avoiding degradation and efficiency losses

Approach:

- Rapid, depth selective laser annealing
- Surface near layer modification
- Protecting substrate from thermal impact [3]

Experimental Approach

Sample Structure

- Planar n-type SHJ substrates
 - Front side intrinsic / p-type doped amorphous silicon layer stack a-Si:H (i/p)
- TCO Variation:
 - Oxygen-rich indium tin oxide (ITO)
 - Aluminum doped zinc oxide (AZO)

Annealing

- Pulsed ns-laser processes at three different wavelengths (photon energy \approx TCO bandgap energy):
 - $\lambda = 248$ nm
 - $\lambda = 308$ nm
 - $\lambda = 343$ nm
- Hotplate: 10 min at temperatures from 50°C to 400°C

Characterization

- Modulated photoluminescence (PL) [4] $\rightarrow iV_{\text{OC}}$
- Four point probe measurements $\rightarrow R_{\text{sheet}}$

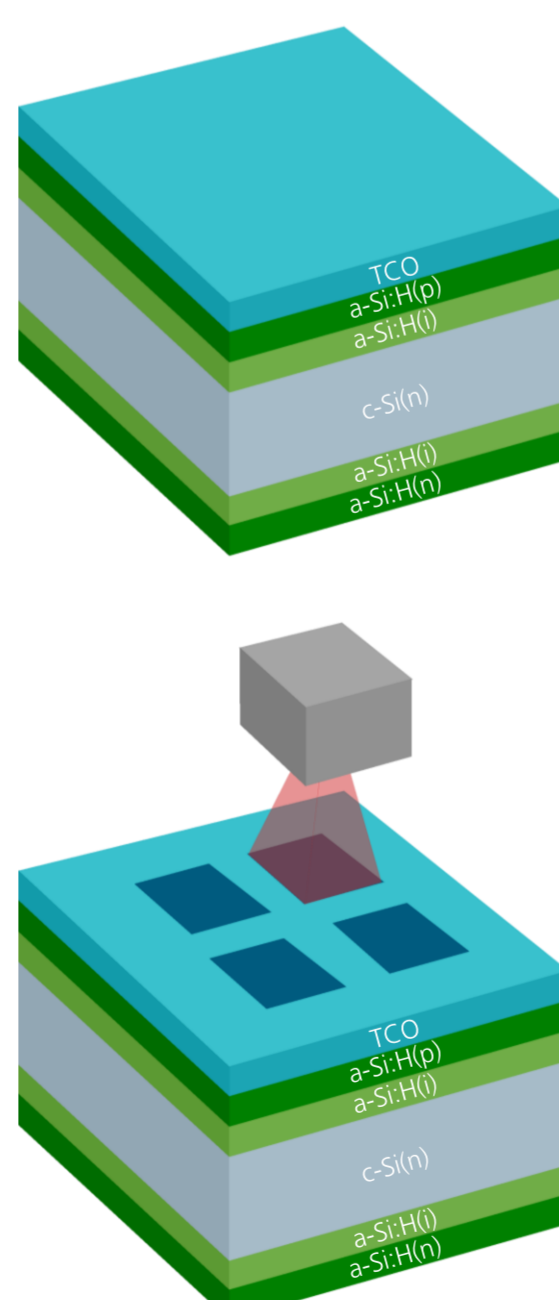


Fig. 2: Schematic illustration of sample structure and laser annealing experimental procedure.

Results

a) PL images of lasered samples

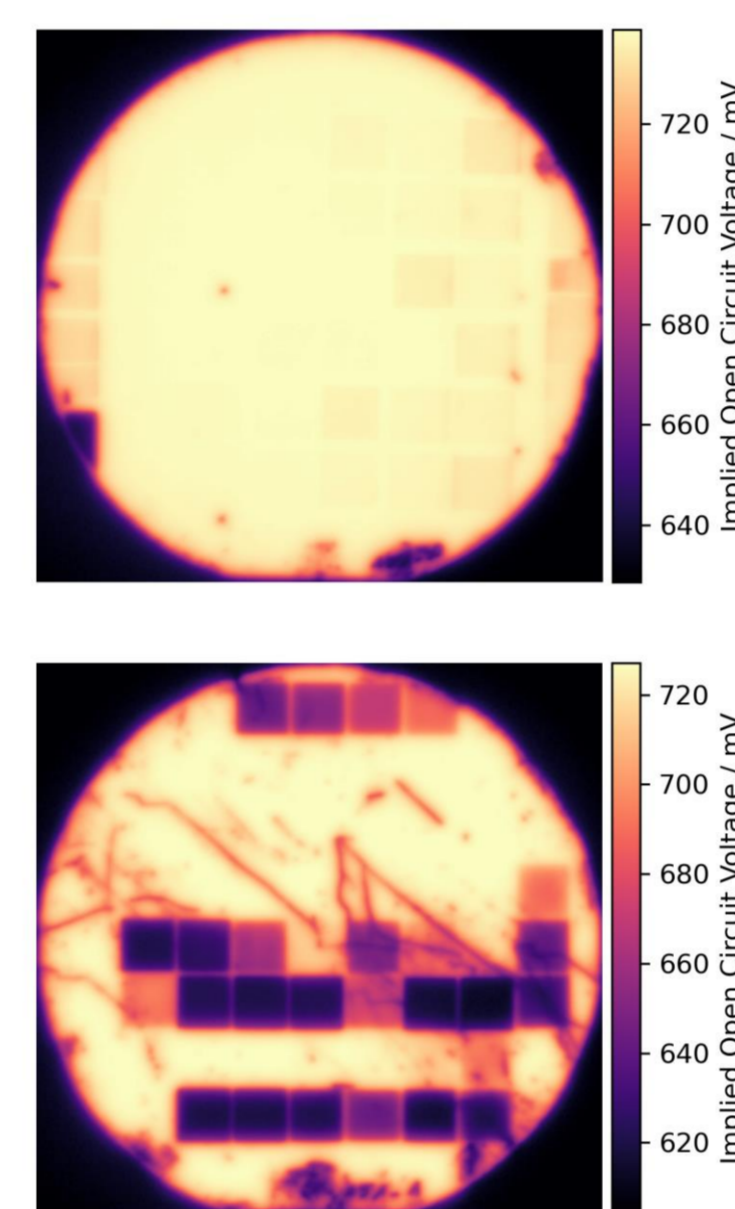
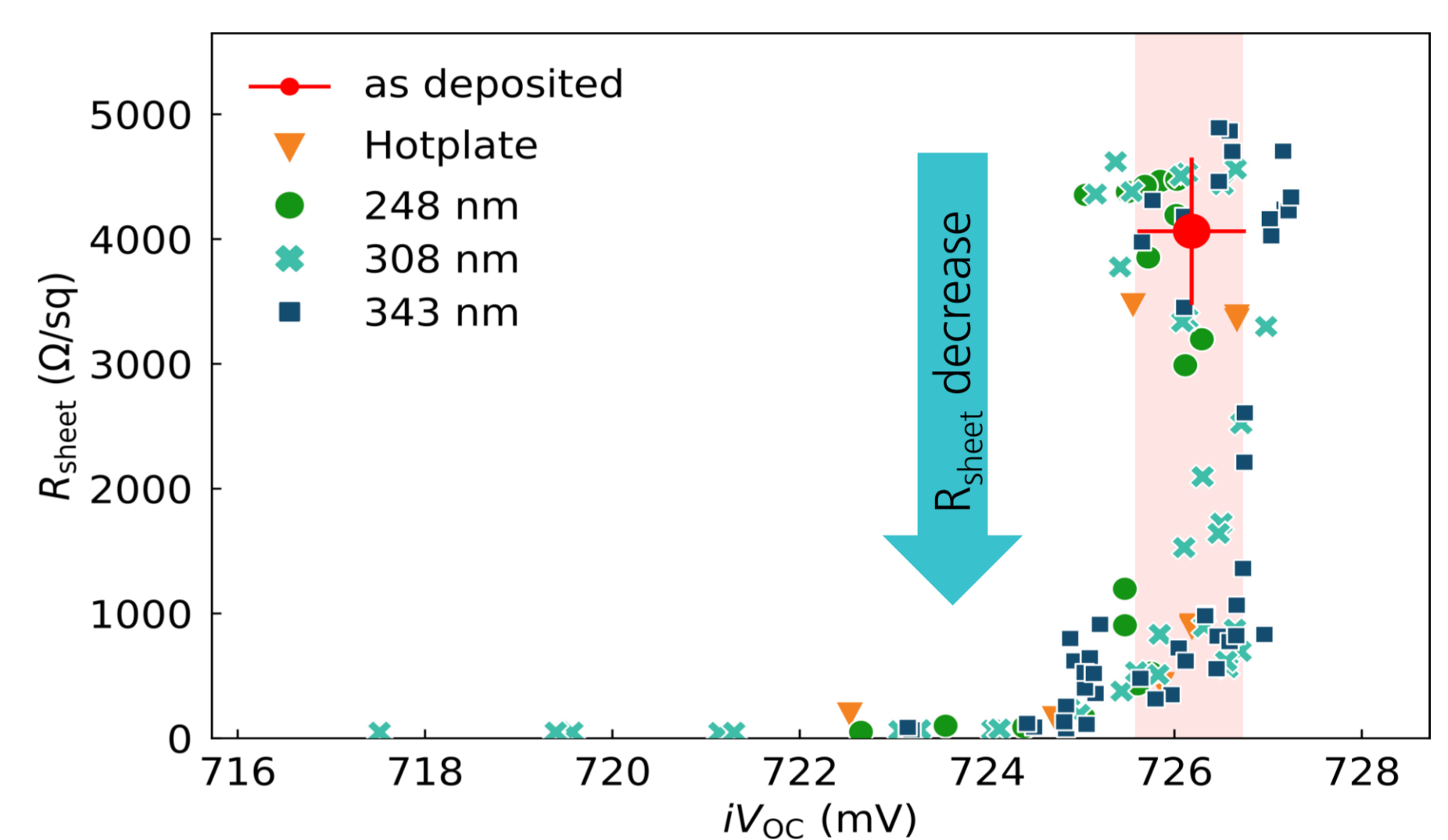
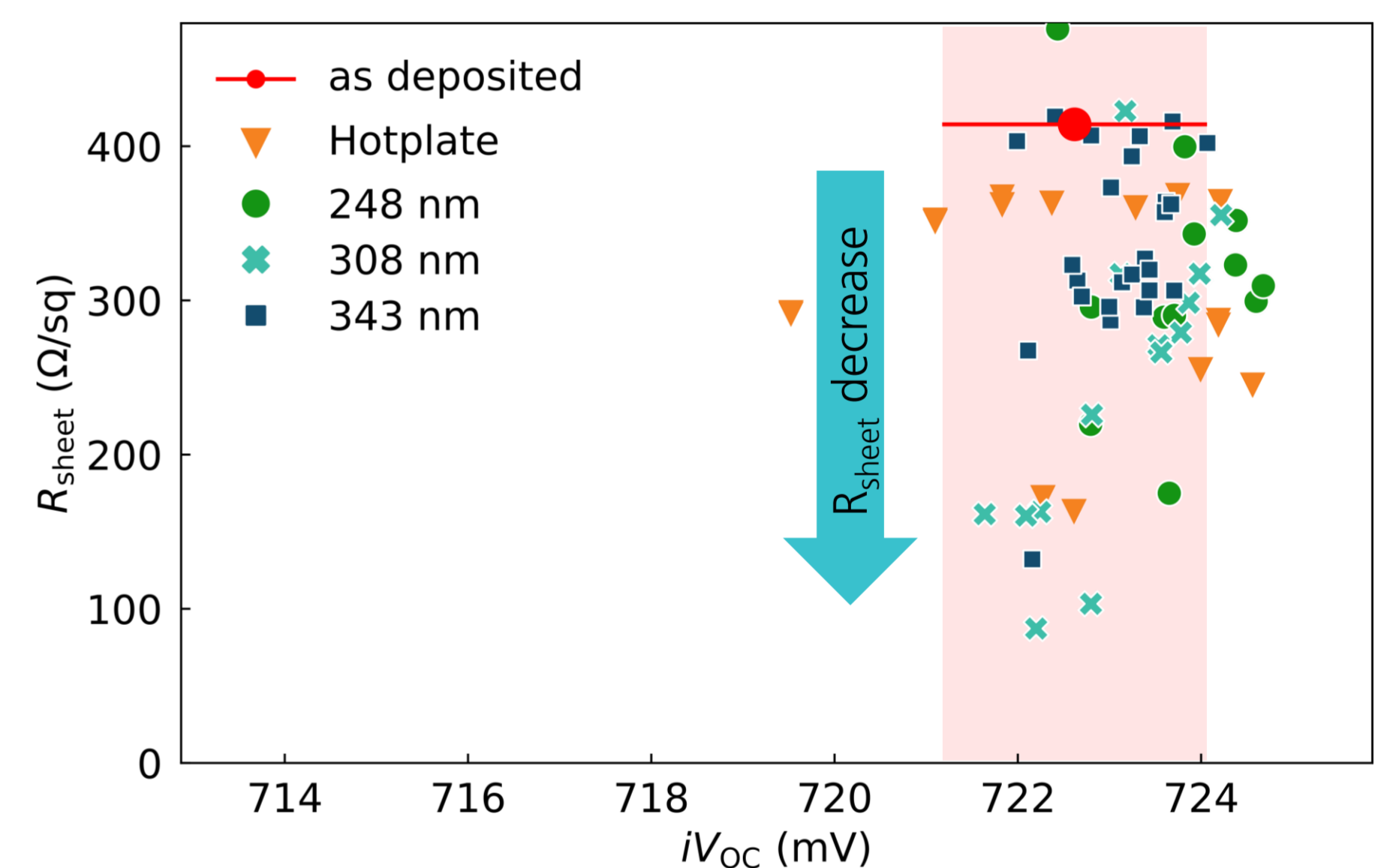


Fig. 3: a) Exemplary PL images showing areas of no/minor degradation (top) and strong degradation (bottom) of the a-Si:H layer after laser annealing. Measurements of TCO R_{sheet} in combination with iV_{OC} for b) substrates with ITO and c) the AZO thin film. Measurements after annealing by the three different UV wavelengths as well as for the hotplate annealing are shown.

b) ITO: R_{sheet} as a function of substrate iV_{OC}



c) AZO: R_{sheet} as a function of substrate iV_{OC}



- UV ns-laser anneal leads to significant R_{sheet} decrease for different TCO types:
 - ITO: $R_{\text{sheet}} = 4060 \text{ } \Omega/\text{sq} \rightarrow 50 \text{ } \Omega/\text{sq}$
 - AZO: $R_{\text{sheet}} = 414 \text{ } \Omega/\text{sq} \rightarrow 90 \text{ } \Omega/\text{sq}$
 - Significantly reduced R_{sheet} while maintaining initial iV_{OC} level
 - Comparable to hotplate annealing
- Fast alternative process to conventional thermal processes
- Potential of enabling indium free TCOs, requiring higher annealing temperatures for solar cells [5]
- Potential for TCO annealing on more temperature sensitive substrates (e.g. perovskite solar cells)

Summary and Conclusion

- Reduction in R_{sheet} of ITO and AZO layers on temperature sensitive SHJ substrates by UV ns-laser annealing
- R_{sheet} is reduced significantly without compromising the iV_{OC}
- Damage free laser annealing of TCO thin films
- Laser processes as fast alternative to hotplate annealing
- Potential of enabling indium-free TCOs for solar cells
- Potential of enabling TCO anneal on T-sensitive perovskite solar cells

[1] C. Messmer, et al., *Prog. Photovoltaics* (2022)
 [2] L. Tutsch et al., *Prog. Photovoltaics* (2021)
 [3] J. Nomoto et al. *NPG Asia Materials* (2022)
 [4] J. M. Greulich et al., *AIP Conference proceedings* (2022)
 [5] W. Yang et al., *Thin Solid Films* (2010)